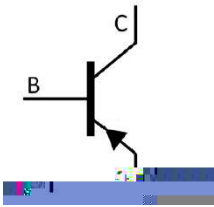


JF K\$*) * GE G` Silicon PNP transistor in a SOT-323 Plastic Package.

9: / (. N
High current, low voltage complementary pair with BC817W.

General purpose switching and amplification.

/ Equivalent Circuit



PIN1 Emitter PIN 2 Base PIN 3 Collector

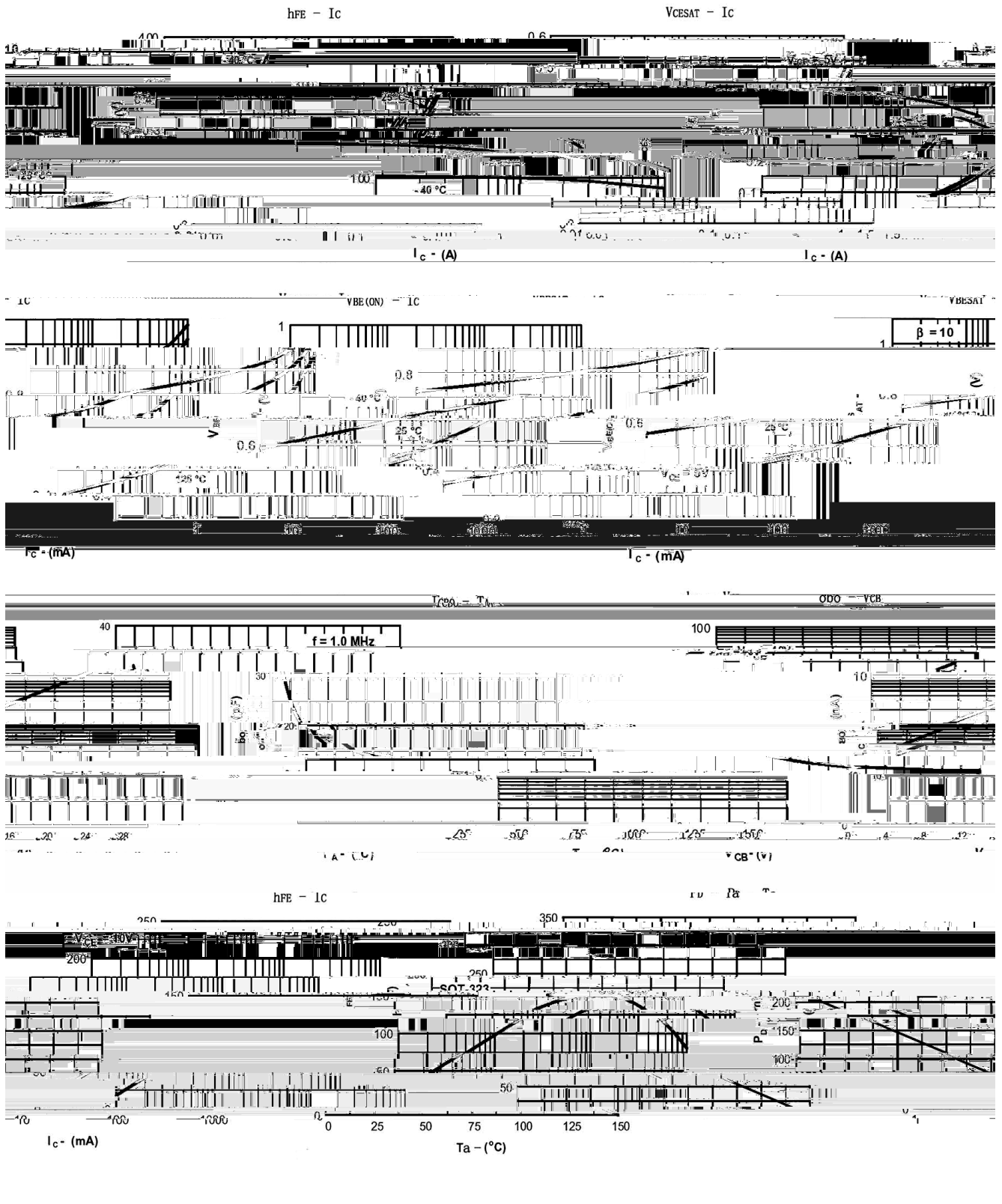
б)8A.5)EEW̄y

/ Absolute Maximum Ratings(Ta=25)

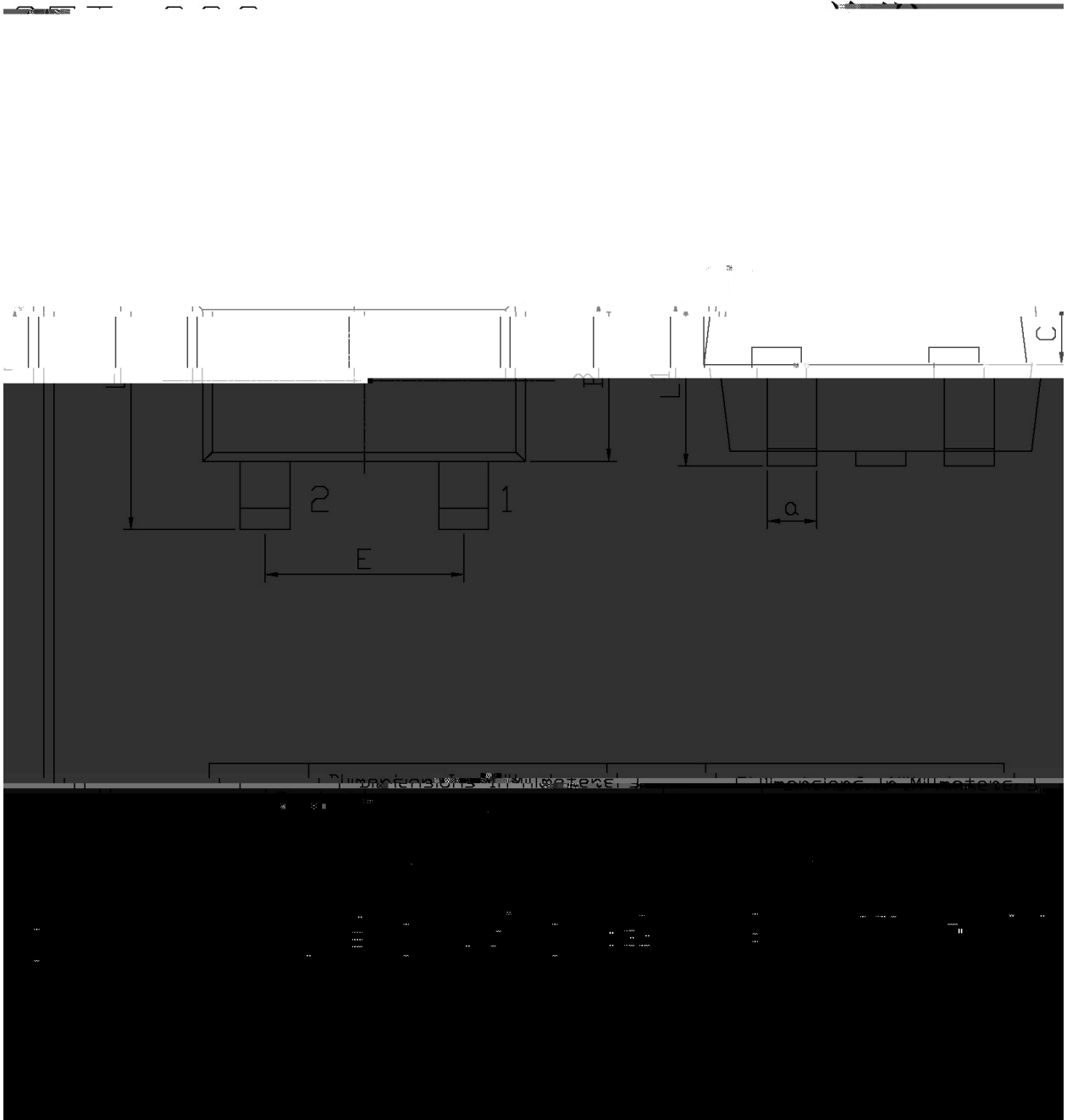
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Peak Collector Current - Continuous	I_{CM}	-1.0	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-1.0V$ $I_C=-100mA$	100		600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$			-0.7	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-1.0V$ $I_C=-500mA$			-1.2	V
Transition Frequency	f_T	$V_{CE}=-5V$ $I_C=-10mA$ $f=100MHz$	80			MHz
Collector Capacitance	C_C	$V_{CB}=-10V$ $I_E=I_C=0$ $f=1.0MHz$		10		pF

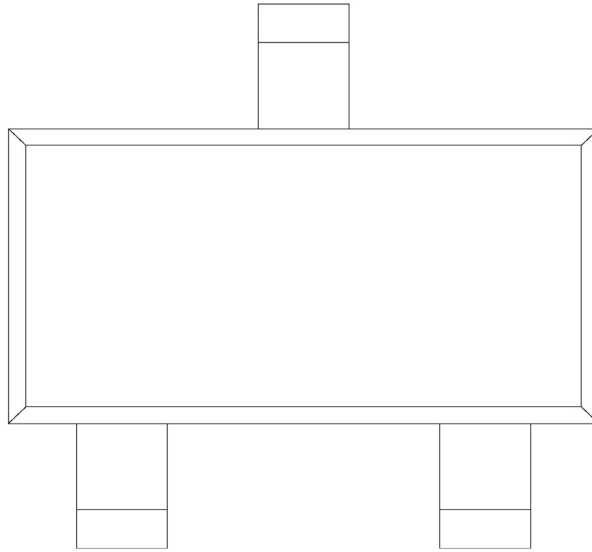
/ Electrical Characteristic Curve



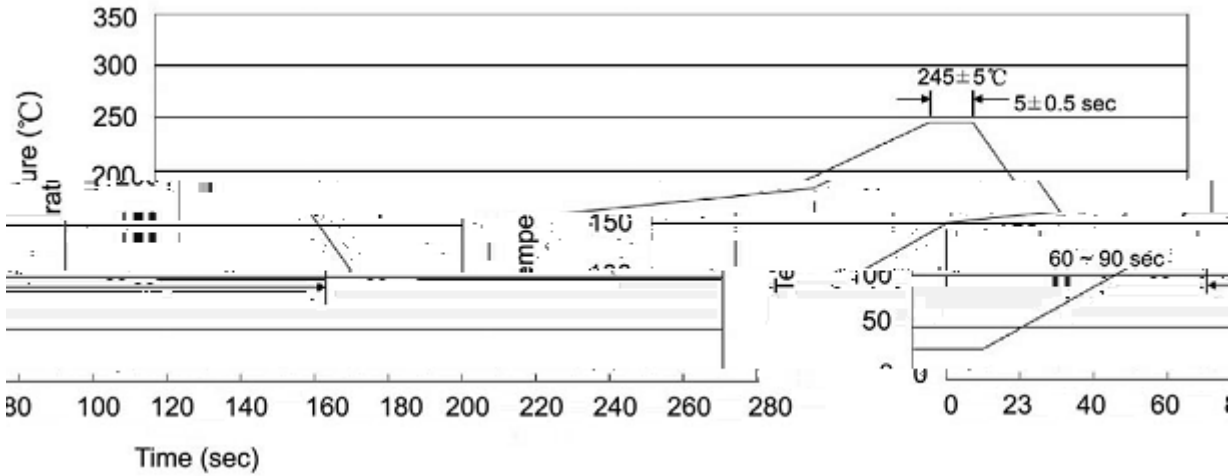
/ Package Dimensions



/ Marking Instructions



() /



Note:

- | | | | | | |
|---|--------|-----|------------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245..5 | | 5..0.5sec; | | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260..5 10..1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

/ Notices